

MMJ75B8F00xx

2023/06/14

Features

Field Stop Trench gate IGBT、Low Collector-Emitter saturation voltage、High short circuit capability
Low switching losses

Version

STD

Application

General-purpose inverter, For EV

Status

Mass production

Specifications

Gate-Emitter voltage VCES [V]	Collector current IC [A]	Collector- Emitter saturation voltage VCE(sat) @Tj=25deg C typical limit	Collector- Emitter saturation voltage VCE(sat) @Tj=25deg C upper limit	Gate Voltage VGES [V]	Gate-Emitter threshold voltage VGE(th) lower limit [V]	Gate-Emitter threshold voltage VGE(th) upper limit [V]
--	-----------------------------------	--	--	-----------------------------	---	---

MMJ75B8F00xx

2023/06/14

		[V]	[V]			
750	275	1.30	1.60	-20~20	5.10	6.50
Internal gate resistor Rgint typical limit [Ω]		Die size X [mm]	Die size Y [mm]		Junction temperature Tj [deg.C]	
1.7		10.60	10.60		-40~175	

NOTE

In the case of EV, please contact our office.